

## 30V/3.6A N-Channel Enhancement Mode Field Effect Transistor

### **General Description**

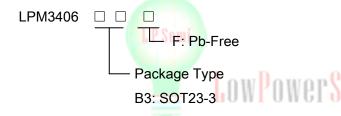
The LPM3406 is N-channel logic enhancement mode power field effect transistor, which are produced by using high cell density, DMOS trench technology.

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This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suitable for low voltage applications, notebook computer power management and other battery powered circuits where high-side switching is needed.

### **Order Information**



#### **Features**

- 30V/3A, R<sub>DS(ON)</sub>=48mΩ(Typ.)@VGS=4.5V
- 30V/3.6A, R<sub>DS(ON)</sub>=36mΩ(Typ.)@VGS=10V
- Super high density cell design for extremely low R<sub>DS(ON)</sub>
- SOT23 Package

### **Applications**

- ♦ Portable Media Players/MP3 players
- ♦ Cellular and Smart mobile phone
- ♦ LCD
- ♦ DSC Sensor
- ♦ Wireless Card

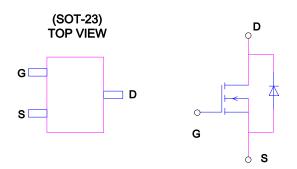
### Marking Information

Device	Marking	Package	Shipping				
LPM3406B3F	LPS M6YWX	SOT23	3K/REEL				
Marking indication:							
Y:Production year W:Production week X:Production batch							

### **Pin Description**

Pin Number	Pin Description			
1	Gate Pin			
2	Source Pin			
3	Drain Pin			

### Pin Configurations





# **Absolute Maximum Ratings**

Absolute Maximum Ratings TA=25°C Unless Otherwise noted								
Parameter		Symbol		Maximum		Units		
Drain-Source Voltage		VDS		30		V		
Gate-Source Voltage		VGS		±20		V		
Continuous Drain	TA=25°C	ID		3.6 2.9		A		
Current	TA=70°C							
Pulsed Drain Current		IDM		15				
Power Dissipation	TA=25°C	PD		1.4 0.9		w		
	TA=70°C							
Junction and Storage Temper	TJ, TSTG		-55 to 150			°C		
L P Semi Thermal Characteristics								
Parameter Parameter				Symbol	開盟	Тур.	Units	
Maximum Junction-to-Ambient			R0JA 125			°C/W		



LPM3406

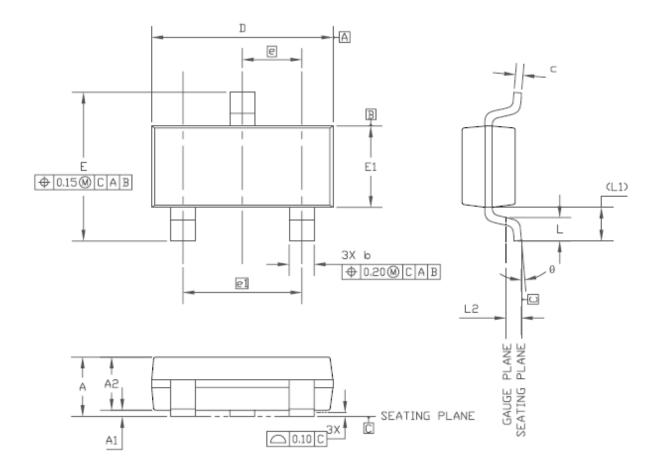
# **Electrical Characteristics**

Symbol	Parameter	Condition	Min.	Тур.	Max.	Units
STATIC PA	ARAMETER			-		
BVDSS	Drain-Source Breakdown Voltage	ID=250µ A , VGS=0V	30			V
IDSS		VDS=16V,VGS=0V			1	
	Zero-Gate Voltage Drain Current	TJ=55°C			5	μA
IGSS	Gate-Body Leakage Current	VDS=0V,VGS=±8V			100	nA
VGS(th)	Gate Threshold Voltage	Gate Threshold Voltage VDS=VGS,ID=250µA		1.8	2.5	V
		VGS=10V, ID=3.6A	36			- m0
RDS(ON)	Static Drain-Source On-Resistance	TJ=125°C		58		mΩ
		VGS=4.5V, ID=3A		48		mΩ
<b>g</b> fs	Forward Transconductance	VDS=5V,ID=3A		11		S
VSD	Diode Forward Voltage	IS=1A,VGS=0V		0.76	1	V
IS	Maximum Body-Diode Continuous Currer			1.5	А	
DYNAMIC P	ARAMETERS					
Ciss	Input Capacitance			180		pF
C <sub>OSS</sub>	Output Capacitance	VDS=10V,VGS=0V f = 1MHz		35		pF
Crss	Reverse Transfer Capacitance			23		pF
Rg	Gate Resistance	VDS=0V,VGS=0V f = 1MHz	导	3.5		Ω
SWITCHING	PARAMETERS	<u>.</u>				
Qg	Total Gate Charge			4.1		nC
Qgs	Gate Source Charge	VDS=10V,VGS=4.5V		0.55		nC
Qgd	Gate Drain Charge	ID-3A		1		nC
t <sub>D(ON)</sub>	Turn-On Delay Time			4.5		nS
tr	Turn-On Rise Time	VDS=10V,VGS=5V		1.5		nS
t <sub>D(OFF)</sub>	Turn-Off Delay Time	RL=2.7Ω		18.5		nS
tf	Turn-Off Fall Time			15.5		nS
trr	Body-Diode Reverse Recovery Time	IF=3A,d I/dt=100/µS		7.5		nS
Qrr	Body-Diode Reverse Recovery Charge	IF=3A,d I/dt=100/µS		2.5		nC

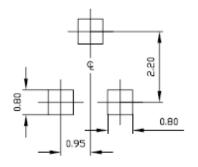


# **Packaging Information**





RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES				
a i midolla	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.75		1.17	0.030		0.046		
A1	0.05	_	0.15	0.002		0.006		
A2	0.70	0.85	1.02	0.028	0.033	0.040		
b	0.30		0.50	0.012		0.020		
С	0.08		0.20	0.003		0.008		
D	2.80	2.90	3.04	0.110	0.114	0.120		
E	2.10		2.64	0.083		0.104		
E1	1.20	1.30	1.40	0.047	0.051	0.055		
e	0.95 BSC				0.037 BSC			
e1	1.90 BSC			0.075 BSC				
L	0.40	0.50	0.60	0.016	0.020	0.024		
L1	0.54 REF			0.021REF				
L.2	0.25			0.010				
θ1	00		80	00		80		

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